

HiPerFRED²

$$V_{RRM} = 400V$$

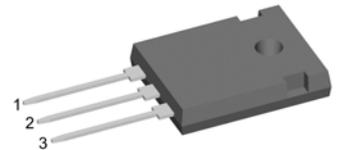
$$I_{FAV} = 2x \quad 30A$$

$$t_{rr} = 45ns$$

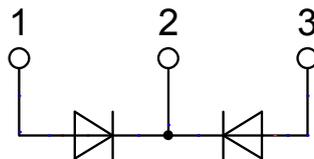
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DPG60C400HB



Backside: cathode

**Features / Advantages:**

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

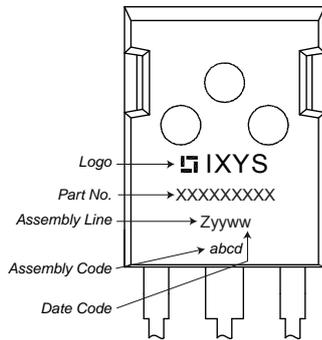
Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

| Fast Diode | | | | Ratings | | |
|------------|--|---|-------------------------|---------|------|------------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| V_{RSM} | max. non-repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 400 | V |
| V_{RRM} | max. repetitive reverse blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 400 | V |
| I_R | reverse current, drain current | $V_R = 400 V$ | $T_{VJ} = 25^{\circ}C$ | | 1 | μA |
| | | $V_R = 400 V$ | $T_{VJ} = 150^{\circ}C$ | | 0.2 | mA |
| V_F | forward voltage drop | $I_F = 30 A$ | $T_{VJ} = 25^{\circ}C$ | | 1.41 | V |
| | | | | | 1.69 | V |
| | | $I_F = 60 A$ | $T_{VJ} = 150^{\circ}C$ | | 1.13 | V |
| | | | | | 1.46 | V |
| I_{FAV} | average forward current | $T_C = 135^{\circ}C$ rectangular $d = 0.5$ | $T_{VJ} = 175^{\circ}C$ | | 30 | A |
| V_{FO} | threshold voltage | } for power loss calculation only | $T_{VJ} = 175^{\circ}C$ | | 0.76 | V |
| r_F | slope resistance | | | | 10.7 | m Ω |
| R_{thJC} | thermal resistance junction to case | | | | 0.95 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | 0.25 | | K/W |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 160 | W |
| I_{FSM} | max. forward surge current | $t = 10 ms; (50 Hz), sine; V_R = 0 V$ | $T_{VJ} = 45^{\circ}C$ | | 360 | A |
| C_J | junction capacitance | $V_R = 200 V \quad f = 1 MHz$ | $T_{VJ} = 25^{\circ}C$ | | 39 | pF |
| I_{RM} | max. reverse recovery current | } $I_F = 30 A; V_R = 270 V$ $-di_F/dt = 200 A/\mu s$ | $T_{VJ} = 25^{\circ}C$ | | 4 | A |
| t_{rr} | reverse recovery time | | $T_{VJ} = 125^{\circ}C$ | | 8.5 | A |
| | | | $T_{VJ} = 25^{\circ}C$ | | 45 | ns |
| | | | $T_{VJ} = 125^{\circ}C$ | | 85 | ns |

| Package TO-247 | | | Ratings | | | |
|----------------|------------------------------|----------------------------|---------|------|------|------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal ¹⁾ | | | 50 | A |
| T_{VJ} | virtual junction temperature | | -55 | | 175 | °C |
| T_{op} | operation temperature | | -55 | | 150 | °C |
| T_{stg} | storage temperature | | -55 | | 150 | °C |
| Weight | | | | 6 | | g |
| M_D | mounting torque | | 0.8 | | 1.2 | Nm |
| F_C | mounting force with clip | | 20 | | 120 | N |

Product Marking



Part number

- D = Diode
- P = HiPerFRED
- G = extreme fast
- 60 = Current Rating [A]
- C = Common Cathode
- 400 = Reverse Voltage [V]
- HB = TO-247AD (3)

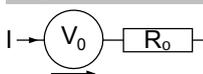
| Ordering | Part Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-------------|--------------------|---------------|----------|----------|
| Standard | DPG60C400HB | DPG60C400HB | Tube | 30 | 505825 |

| Similar Part | Package | Voltage class |
|--------------|--------------|---------------|
| DPG60C400QB | TO-3P (3) | 400 |
| DPG80C400HB | TO-247AD (3) | 400 |

Equivalent Circuits for Simulation

* on die level

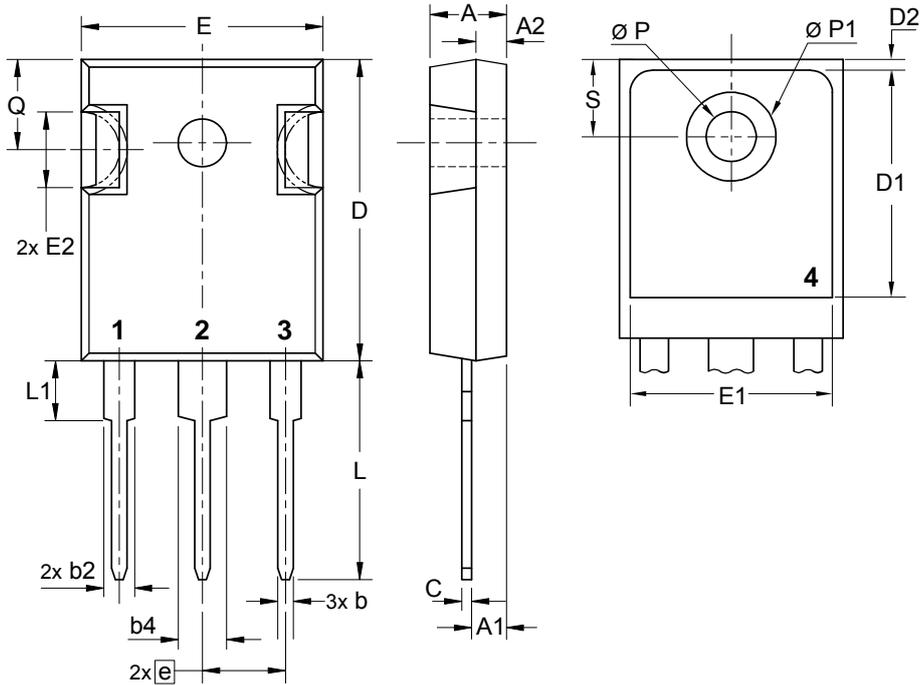
$T_{VJ} = 175\text{ °C}$



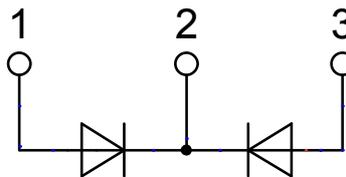
Fast Diode

| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.76 | V |
| $R_{0\ max}$ | slope resistance * | 8.1 | mΩ |

Outlines TO-247



| Sym. | Inches | | Millimeter | |
|------|-----------|-------|------------|-------|
| | min. | max. | min. | max. |
| A | 0.185 | 0.209 | 4.70 | 5.30 |
| A1 | 0.087 | 0.102 | 2.21 | 2.59 |
| A2 | 0.059 | 0.098 | 1.50 | 2.49 |
| D | 0.819 | 0.845 | 20.79 | 21.45 |
| E | 0.610 | 0.640 | 15.48 | 16.24 |
| E2 | 0.170 | 0.216 | 4.31 | 5.48 |
| e | 0.215 BSC | | 5.46 BSC | |
| L | 0.780 | 0.800 | 19.80 | 20.30 |
| L1 | - | 0.177 | - | 4.49 |
| Ø P | 0.140 | 0.144 | 3.55 | 3.65 |
| Q | 0.212 | 0.244 | 5.38 | 6.19 |
| S | 0.242 BSC | | 6.14 BSC | |
| b | 0.039 | 0.055 | 0.99 | 1.40 |
| b2 | 0.065 | 0.094 | 1.65 | 2.39 |
| b4 | 0.102 | 0.135 | 2.59 | 3.43 |
| c | 0.015 | 0.035 | 0.38 | 0.89 |
| D1 | 0.515 | - | 13.07 | - |
| D2 | 0.020 | 0.053 | 0.51 | 1.35 |
| E1 | 0.530 | - | 13.45 | - |
| Ø P1 | - | 0.29 | - | 7.39 |



Fast Diode

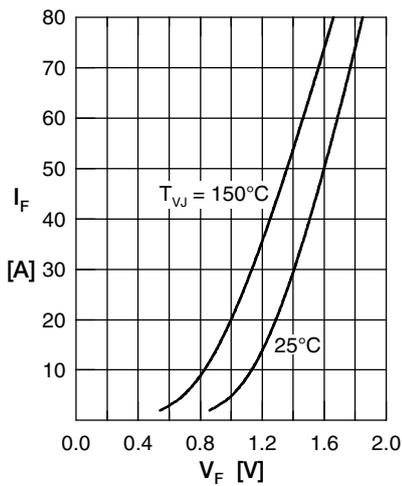


Fig. 1 Forward current I_F versus V_F

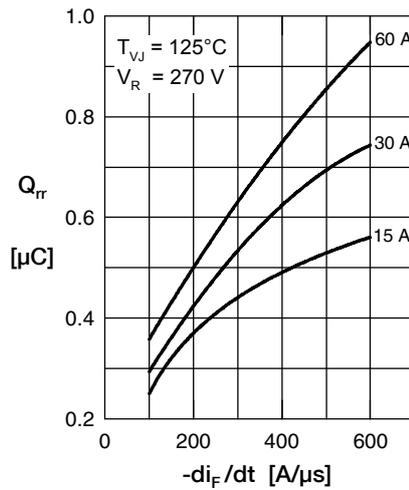


Fig. 2 Typ. reverse recov. charge Q_{rr} versus $-di_F/dt$

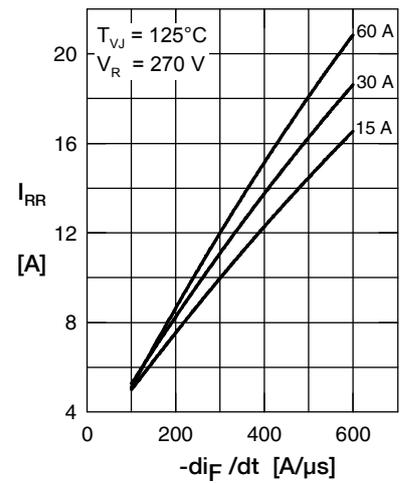


Fig. 3 Typ. reverse recovery current I_{RR} versus $-di_F/dt$

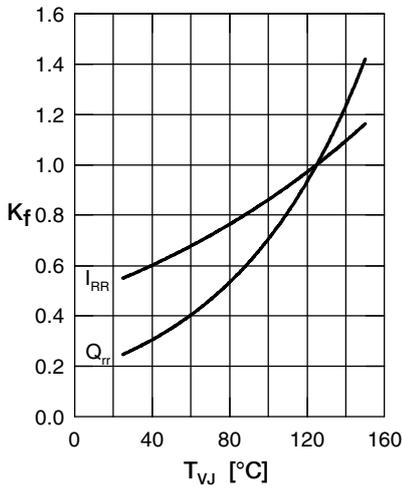


Fig. 4 Typ. dynamic parameters Q_{rr} , I_{RR} versus T_{VJ}

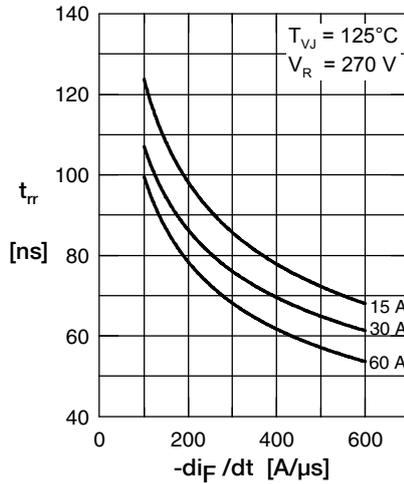


Fig. 5 Typ. reverse recov. time t_{rr} versus $-di_F/dt$

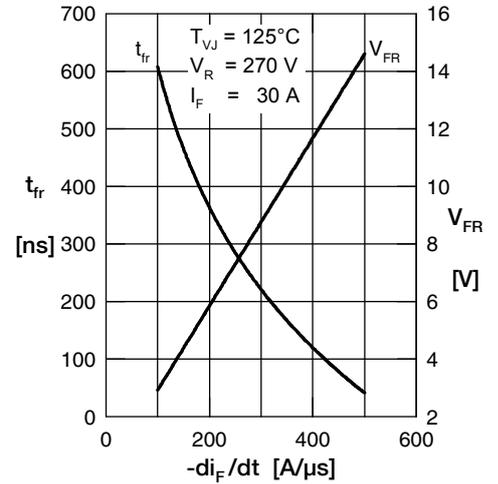


Fig. 6 Typ. forward recov. voltage V_{FR} & time t_{fr} versus di_F/dt

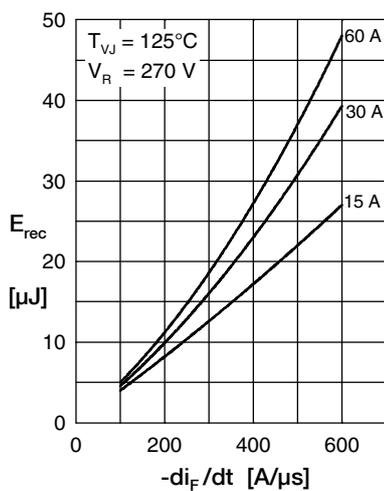


Fig. 7 Typ. recovery energy E_{rec} versus $-di_F/dt$

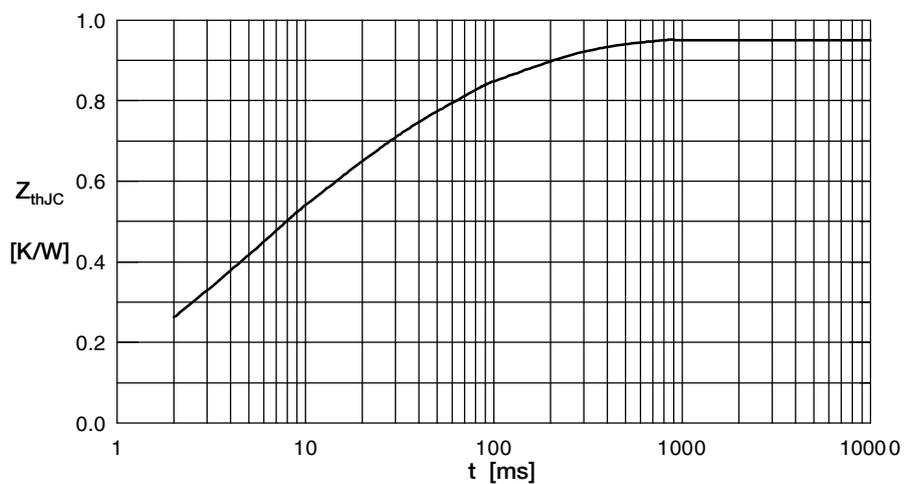


Fig. 8 Transient thermal impedance junction to case

Данный компонент на территории Российской Федерации

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<http://moschip.ru/get-element>

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9